

Form PTO-1449 U.S. DEPARTMENT OF COMMERCE (REV. 7-80) PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE STATEMENT <i>(Use several sheets if necessary)</i>								O I P E JUL 23 2001 C161 PATENT & TRADEMARK OFFICE		ATTY. DOCKET NO.: UF-222XC2D2 SERIAL NO. 09/735,217		
								APPLICANT(S): Tim Anderson				
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U.S. PATENT DOCUMENTS												
*EXAMINER INITIAL		DOCUMENT NUMBER					DATE	NAME		CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
LAC	AA	5	6	2	5	2	0	2	4/1997	Chai		
	AB											10/23/00
	AC											JUL 26 2001
	AD											RE-SEARCHED
	AE											MAIL ROOM
	AF											
FOREIGN PATENT DOCUMENTS												
		DOCUMENT NUMBER					DATE	COUNTRY		CLASS	SUBCLASS	TRANSLATION YES NO
LAC	AG	0	8	4	6	7	9	1	10/1998	EPO		
	AH											
	AI											
	AJ											
OTHER PRIOR ART <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>												
LAC	AK	1	S. Nakamura, M. Senoh, S. Nagahama, N. Iwasa, et al., "Continuous-wave operation of InGaN/GaN/AlGaN-based laser diodes grown on GaN substrates" 1998 <i>Appl. Phys. Lett.</i> , 72, 16, 2014.									
LAC	AL	2	J.C. Zolper, R.J. Shul, A.G. Baca, R.G. Wilson, S.J. Pearton, R.A. Stall, "Ion-Implanted GaN junction field effect transistor" 1996 <i>Appl. Phys. Lett.</i> , 68, (16).									
VAC	AM	3	H. Morkoc, S. Strite, G.B. Gao, M.E. Lin, B. Sverdlov and M. Burns, "Large-band-gap SiC, III-V nitride, and II-VI ZnSe based semiconductor device technologies" 1994 <i>J. Appl. Phys.</i> 76, 1367.									
VAC	AN	4	T.P. Chow and Tyagi, "Wide Bandgap Compound Semiconductors for Superior High-Voltage Unipolar Power Devices" 1994 IEEE Trans. Electron Devices, 41, 1481.									
VAC	AO	5	Grzegory, J. Jun., S. Kurowski, M. Bockowski, and S. Porowski, "Crystal Growth of III-N compounds under high nitrogen pressure" 1993 <i>Physica B</i> , 185, 99.									
VAC	AP	6	Yu. V. Melnik, K.V. Vassilevski, I.P. Nikitina, A.I. Babamin, V. Yu. Davydov, V.A. Dmitriev, "Physical Properties of Bulk GaN Crystals Grown by HVPE" 1997 MIJ-NSR, Vol. 2, Art. 39.									
VAC	AQ	7	O.M. Kryliouk, T.W. Dann, T.J. Anderson, G.P. Maruska, L.D. Zhu, T.J. Daly, M. Lin, P. Norris, H.T. Chai, D.W. Kisker, J.H. Li, K.S. Jones "MOCVD Growth of GaN Films on Lattice-Matched Oxide Substrates" 1997 Mat. Res. Soc. Sym. Proc. Vol. 449 Materials Research Society.									
VAC	AR	8	Olga Kryliouk, Mike Reed, Todd Dann, Tim Anderson, Bruce Chai "Growth of GaN single crystal substrates" 1999 Materials Science and Engineering B59 (1999) 6-11.									
VAC	AS	9	Shuji Nakamura, "InGaN/GaN/AlGaN-Based Laser Diodes with an Estimated Lifetime of Longer Than 10,000 Hours" 1998 MRS Bulletin.									
EXAMINER	<i>ZAC</i>								DATE CONSIDERED 7/16/03			
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.												

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